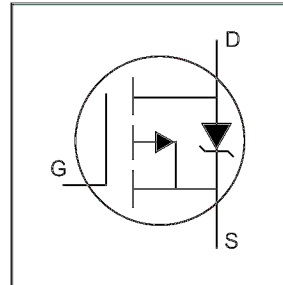


- Ultra Low On-Resistance
- P-Channel
- Surface Mount (IRFR9120N)
- Straight Lead (IRFU9120N)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



$$V_{DS} = -100V$$

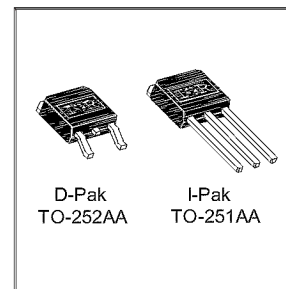
$$R_{DS(on)} = 0.48\Omega$$

$$I_D = -6.6A$$

## Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



D-Pak  
TO-252AA

I-Pak  
TO-251AA

## Absolute Maximum Ratings

|                           | Parameter                                 | Max.                   | Units |
|---------------------------|-------------------------------------------|------------------------|-------|
| $I_D @ T_C = 25^\circ C$  | Continuous Drain Current, $V_{GS} @ -10V$ | -6.6                   | A     |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ -10V$ | -4.2                   |       |
| $I_{DM}$                  | Pulsed Drain Current ①                    | -26                    |       |
| $P_D @ T_C = 25^\circ C$  | Power Dissipation                         | 40                     | W     |
|                           | Linear Derating Factor                    | 0.32                   | W/°C  |
| $V_{GS}$                  | Gate-to-Source Voltage                    | $\pm 20$               | V     |
| $E_{AS}$                  | Single Pulse Avalanche Energy②            | 100                    | mJ    |
| $I_{AR}$                  | Avalanche Current③                        | -6.6                   | A     |
| $E_{AR}$                  | Repetitive Avalanche Energy③              | 4.0                    | mJ    |
| $dv/dt$                   | Peak Diode Recovery $dv/dt$ ③             | -5.0                   | V/ns  |
| $T_J$                     | Operating Junction and                    | -55 to + 150           | °C    |
| $T_{STG}$                 | Storage Temperature Range                 |                        |       |
|                           | Soldering Temperature, for 10 seconds     | 300 (1.6mm from case ) |       |

## Thermal Resistance

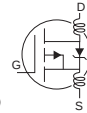
|                 | Parameter                         | Typ. | Max. | Units |
|-----------------|-----------------------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case                  | —    | 3.1  | °C/W  |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB mount)** | —    | 50   |       |
| $R_{\theta JA}$ | Junction-to-Ambient               | —    | 110  |       |

# IRFR/U9120NPbF

International  
IR Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

|                                 | Parameter                            | Min. | Typ.  | Max. | Units              | Conditions                                                                    |
|---------------------------------|--------------------------------------|------|-------|------|--------------------|-------------------------------------------------------------------------------|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | -100 | —     | —    | V                  | $V_{GS} = 0V, I_D = -250\mu A$                                                |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | -0.11 | —    | $V/^\circ\text{C}$ | Reference to $25^\circ\text{C}$ , $I_D = -1\text{mA}$                         |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | —     | 0.48 | $\Omega$           | $V_{GS} = -10V, I_D = -3.9A$ ④                                                |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | -2.0 | —     | -4.0 | V                  | $V_{DS} = V_{GS}, I_D = -250\mu A$                                            |
| $g_{fs}$                        | Forward Transconductance             | 1.4  | —     | —    | S                  | $V_{DS} = -50V, I_D = -4.0A$ ⑥                                                |
| $I_{DSS}$                       | Drain-to-Source Leakage Current      | —    | —     | -25  | $\mu A$            | $V_{DS} = -100V, V_{GS} = 0V$                                                 |
|                                 |                                      | —    | —     | -250 |                    | $V_{DS} = -80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$                         |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —     | 100  | nA                 | $V_{GS} = 20V$                                                                |
|                                 | Gate-to-Source Reverse Leakage       | —    | —     | -100 |                    | $V_{GS} = -20V$                                                               |
| $Q_g$                           | Total Gate Charge                    | —    | —     | 27   | nC                 | $I_D = -4.0A$                                                                 |
| $Q_{gs}$                        | Gate-to-Source Charge                | —    | —     | 5.0  |                    | $V_{DS} = -80V$                                                               |
| $Q_{gd}$                        | Gate-to-Drain ("Miller") Charge      | —    | —     | 15   |                    | $V_{GS} = -10V$ , See Fig. 6 and 13 ④ ⑥                                       |
| $t_{d(on)}$                     | Turn-On Delay Time                   | —    | 14    | —    | ns                 | $V_{DD} = -50V$                                                               |
| $t_r$                           | Rise Time                            | —    | 47    | —    |                    | $I_D = -4.0A$                                                                 |
| $t_{d(off)}$                    | Turn-Off Delay Time                  | —    | 28    | —    |                    | $R_G = 12\Omega$                                                              |
| $t_f$                           | Fall Time                            | —    | 31    | —    |                    | $R_D = 12\Omega$ , See Fig. 10 ④ ⑥                                            |
| $L_D$                           | Internal Drain Inductance            | —    | 4.5   | —    | nH                 | Between lead,<br>6mm (0.25in.)<br>from package<br>and center of die contact ⑤ |
| $L_S$                           | Internal Source Inductance           | —    | 7.5   | —    |                    |                                                                               |
| $C_{iss}$                       | Input Capacitance                    | —    | 350   | —    | pF                 | $V_{GS} = 0V$                                                                 |
| $C_{oss}$                       | Output Capacitance                   | —    | 110   | —    |                    | $V_{DS} = -25V$                                                               |
| $C_{rss}$                       | Reverse Transfer Capacitance         | —    | 70    | —    |                    | $f = 1.0\text{MHz}$ , See Fig. 5 ⑥                                            |



## Source-Drain Ratings and Characteristics

|          | Parameter                              | Min.                                                                        | Typ. | Max. | Units | Conditions                                                     |
|----------|----------------------------------------|-----------------------------------------------------------------------------|------|------|-------|----------------------------------------------------------------|
| $I_S$    | Continuous Source Current (Body Diode) | —                                                                           | —    | -6.6 | A     | MOSFET symbol showing the integral reverse p-n junction diode. |
| $I_{SM}$ | Pulsed Source Current (Body Diode) ①   | —                                                                           | —    | -26  |       |                                                                |
| $V_{SD}$ | Diode Forward Voltage                  | —                                                                           | —    | -1.6 | V     | $T_J = 25^\circ\text{C}, I_S = -3.9A, V_{GS} = 0V$ ④           |
| $t_{rr}$ | Reverse Recovery Time                  | —                                                                           | 100  | 150  | ns    | $T_J = 25^\circ\text{C}, I_F = -4.0A$                          |
| $Q_{rr}$ | Reverse Recovery Charge                | —                                                                           | 420  | 630  | nC    | $di/dt = 100A/\mu s$ ④ ⑥                                       |
| $t_{on}$ | Forward Turn-On Time                   | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ ) |      |      |       |                                                                |

### Notes:

① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )

② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 13\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = -3.9A$ . (See Figure 12)

③  $I_{SD} \leq -4.0A$ ,  $di/dt \leq 300A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 150^\circ\text{C}$

④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

⑤ This is applied for I-PAK,  $L_S$  of D-PAK is measured between lead and center of die contact

⑥ Uses IRF9520N data and test conditions.

\*\* When mounted on 1" square PCB (FR-4 or G-10 Material) .

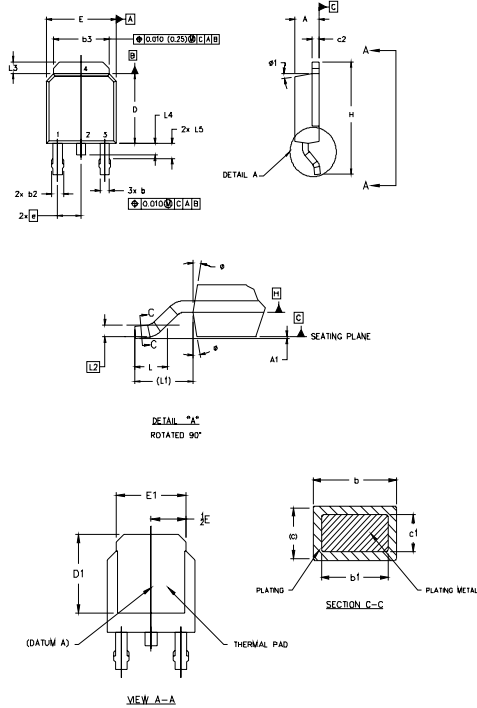
For recommended footprint and soldering techniques refer to application note #AN-994

# IRFR/U9120NPbF

International  
**IR** Rectifier

## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M-1994.
  - 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
  - 3.0 LEAD DIMENSION UNCONTROLLED IN L5.
  - 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.254] FROM THE LEAD TIP.
  - 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .003" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

| SYMBOL | DIMENSIONS          |       |          |       | NOTES                                                                          |
|--------|---------------------|-------|----------|-------|--------------------------------------------------------------------------------|
|        | MILLIMETERS         |       | INCHES   |       |                                                                                |
|        | MIN.                | MAX.  | MIN.     | MAX.  |                                                                                |
| A      | 2.18                | 2.30  | .086     | .094  | LEAD ASSIGNMENTS                                                               |
| A1     |                     | 0.13  |          | .005  |                                                                                |
| b      | 0.64                | 0.89  | .025     | .035  |                                                                                |
| b1     | 0.64                | 0.79  | .025     | 0.031 |                                                                                |
| b2     | 0.76                | 1.14  | .030     | .045  |                                                                                |
| b3     | 4.95                | 5.46  | .195     | .215  | HEXFET<br><br>1.- GATE<br>2.- DRAIN<br>3.- SOURCE<br>4.- DRAIN                 |
| c      | 0.46                | 0.61  | .018     | .024  |                                                                                |
| c1     | 0.41                | 0.56  | .016     | .022  |                                                                                |
| c2     | .046                | 0.89  | .018     | .035  |                                                                                |
| D      | 3.97                | 6.27  | .155     | .245  |                                                                                |
| D1     | 5.21                | -     | .205     | -     | 4                                                                              |
| E      | 6.35                | 6.73  | .250     | .265  |                                                                                |
| E1     | 4.32                | -     | .170     | -     | 4                                                                              |
| e      | 2.29                |       | .090 BSC |       |                                                                                |
| H      | 9.40                | 10.41 | .370     | .410  | IGBTs, CoPACK<br><br>1.- GATE<br>2.- COLLECTOR<br>3.- EMITTER<br>4.- COLLECTOR |
| L      | 1.40                | 1.76  | .055     | .070  |                                                                                |
| L1     | 2.74 REF. .108 REF. |       |          |       |                                                                                |
| L2     | 0.051 BSC           |       | .020 BSC |       |                                                                                |
| L3     | 0.89                | 1.27  | .035     | .050  |                                                                                |
| L4     |                     | 1.02  |          | .040  | 3                                                                              |
| L5     | 1.14                | 1.52  | .045     | .060  |                                                                                |
| ø      | 0"                  | 10"   | 0"       | 10"   |                                                                                |
| ø1     | 0"                  | 15"   | 0"       | 15"   |                                                                                |

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

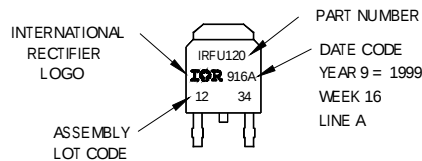
IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

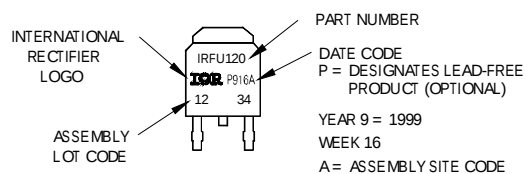
## D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON VW16, 1999  
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position  
indicates "Lead-Free"



OR

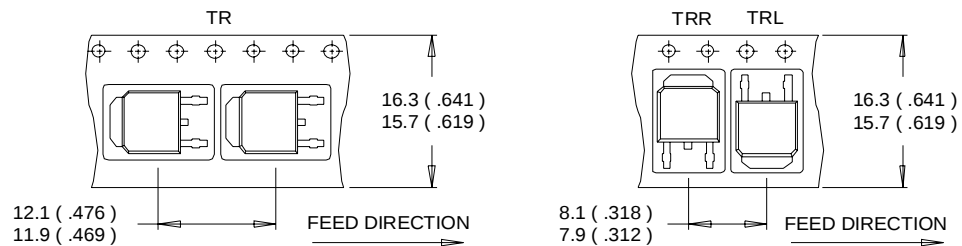


# IRFR/U9120NPbF

International  
**IOR** Rectifier

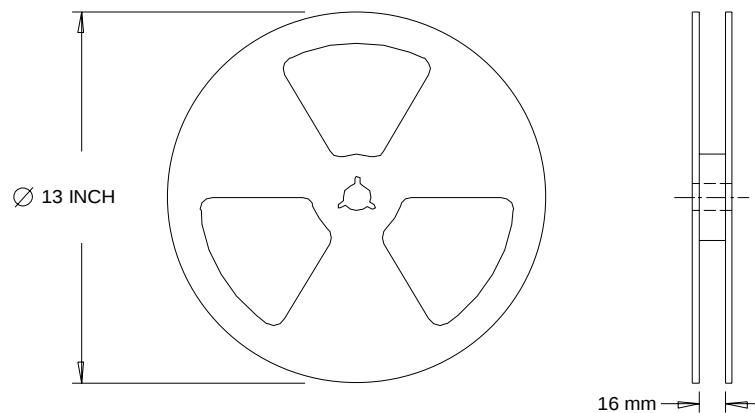
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



### NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



### NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.

International  
**IOR** Rectifier